Exam. Code: 0933 Sub. Code: 6658

2074

B.E. (Electrical and Electronics Engineering) **Third Semester**

PC-EE-303: Analog Electronics

Time al	lowed: 3 Hours Max. Marks:	Max. Marks: 50	
NOTE:	Attempt <u>five</u> questions in all, including Question No. I which is computand selecting two questions from each Section.	lsory	
	x-x-x		
I.			
a)	What in the 1:00		
b)	What is the difference between Avalanche breakdown and Zener breakdown? Find output resistance of BIT for early voltage of 100 M.		
c)	Find output resistance of BJT for early voltage of 100 V and collector current of 1mA. Draw I _D -V _{DS} characteristics of MOSFET.		
ď)	Define slew rate. How it affects Op-Amp performance?	ıA.	
e)	Which type of feedback is applied to the oscillators?		
	[5×2	=10]	
II. a) (Give small signal model of diad		
b)	Give small signal model of diode and derive expression for its dynamic resistance. A silicon diode has a reverse saturation correct.	[5]	
b) A silicon diode has a reverse saturation current of 0.20 pA at 30°C. Find the diode current when it is forward biased by 0.65V at a temperature of 100°C.			
	of 0.03 v at a temperature of 100°C.	[5]	
III. a) (Consider a common emitter circuit using a DEEL		
III. a) Consider a common emitter circuit using a BJT having $I_S = 10^{-15}$ A, a collector resistance $R_C = 6.8 \text{ k}\Omega$ and a power supply = 10V. Determine the value of bias voltage V_{BE} required to operate the transistor at $V_{CE} = 3.2$ V. What is the corresponding value of collector support I_S			
transistor at $V_{CE} = 3.2V$. What is the corresponding and the value of bias voltage V_{BE} required to operate the			
b) \	With the help of suitable diagrams and it is to concettor current Ic?	[5]	
Draw trans	With the help of suitable diagrams, explain how BJT is used as an amplifier and as fer characteristics for CE configuration.	a switch.	
	• • • • • • • • • • • • • • • • • • •	[5]	
IV. a) [Draw device structure and explain physical operation of MOSFET in enhancement multiplication without gate voltage.		
and	without gate voltage.	ode with	
b) F	For a MOSFET with W/L= 8μ m/0.8 μ m, calculate values of V _{GS} and V _{DSmin} needed to uration region with a dc current I _D = 100μ A	[5]	
		[5]	
*7	SECTION B		
V. a) D	Taw and explain equivalent circuit of		
b) D	Define the terms: CMRR, Output offset voltage and Gain bandwidth product.		
171 -> 17	The state of the Gam bandwidth product.	[6]	
VI. a) W	With the help of suitable diagram, explain functioning of integrator and derive expressible places. Plot frequency response of basic and practical integrator.		
us output vo	oltage. Plot frequency response of basic and practical integrator?		
D) D	resign a Phase Shift oscillator using op-amp for output frequency of 1 kHz.	[5]	
		[5]	
a) In	note on following:		
h) D	strumentation Amplifier eak detector	[5]	
D) I'd	Can detector	[5]	
		[5]	